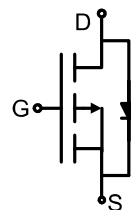


TP40905

P-Channel Enhancement Mosfet

Feature

- -40V, 5A
 $R_{DS(on)} < 85m\Omega @ V_{GS} = -10V$ TYP: 65 m Ω
 $R_{DS(on)} < 120m\Omega @ V_{GS} = -4.5V$ TYP: 90 m Ω
- Advanced Trench Technology
- Lead free product is acquired



Schematic diagram

Application

- Interfacing Switching
- Load Switching
- Power management



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
40P05	TP40P05	Sot-23	7 inch	-	3000

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a = 25^\circ\text{C}$)	I_D	-5	A
Continuous Drain Current ($T_a = 70^\circ\text{C}$)	I_D	-3.5	A
Pulsed Drain Current	I_{DM}	-20	A
Power Dissipation	P_D	2	W
Thermal Resistance from Junction to Ambient ⁽⁴⁾	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-40	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-40V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V,V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.6	-2.5	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =-10V, I _D =-3A	-	65	85	mΩ
		V _{GS} =-4.5V, I _D =-2A	-	90	120	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =-20V, V _{GS} =0V, f =1MHz	-	596	-	pF
Output Capacitance	C _{oss}		-	90	-	
Reverse Transfer Capacitance	C _{rss}		-	70	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =-20V, I _D =-3A, V _{GS} =-10V, R _G =3Ω	-	9	-	ns
Turn-on rise time	t _r		-	8	-	
Turn-off delay time	t _{d(off)}		-	28	-	
Turn-off fall time	t _f		-	10	-	
Total Gate Charge	Q _g	V _{DS} =-20V, I _D =-3A, V _{GS} =-10V	-	14	-	nC
Gate-Source Charge	Q _{gs}		-	2.9	-	
Gate-Drain Charge	Q _{gd}		-	3.8	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =-3A	-	-	1.2	V
Diode Forward current ⁽⁴⁾	I _S		-	-	-4.0	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. Surface Mounted on FR4 Board, $t \leq 10$ sec

Test Circuit

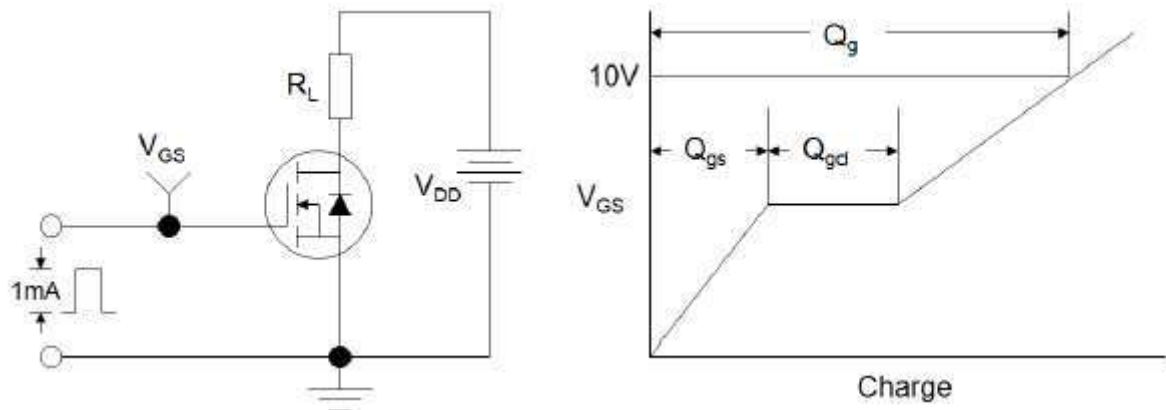


Figure1:Gate Charge Test Circuit & Waveform

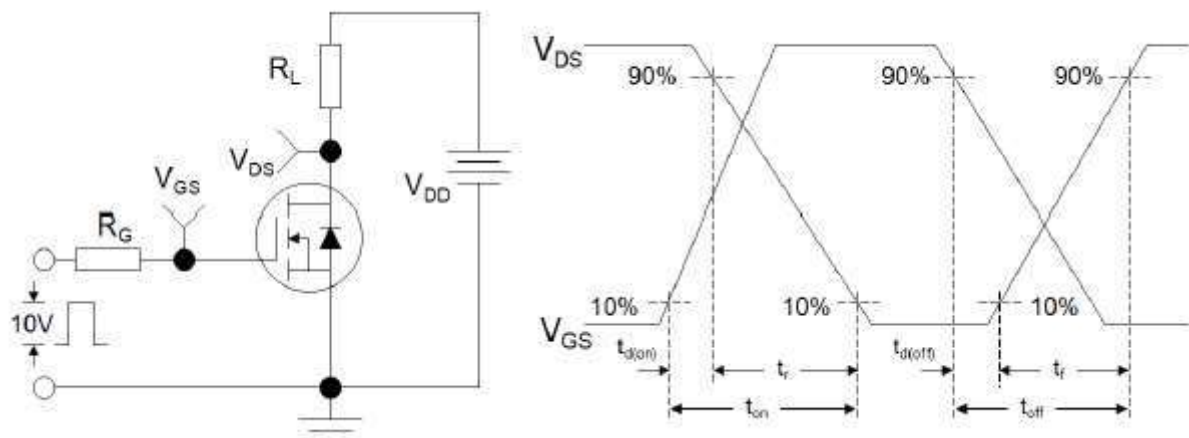


Figure 2: Resistive Switching Test Circuit & Waveforms

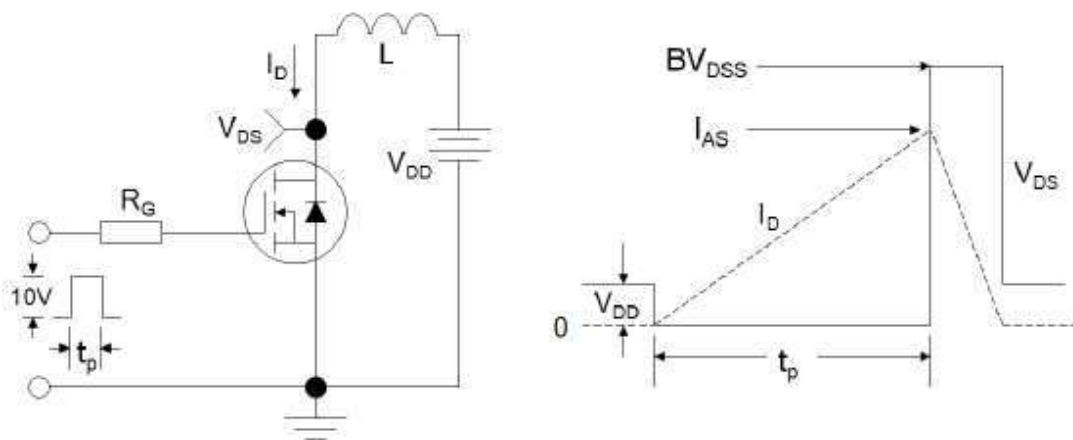


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Typical Electrical and Thermal Characteristics

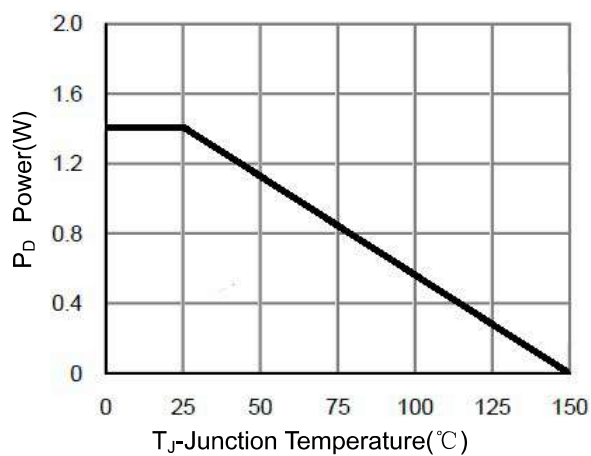


Figure 1 Power Dissipation

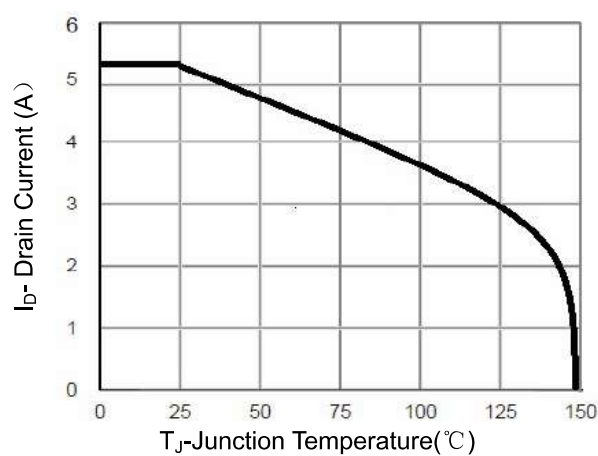


Figure 2 Drain Current

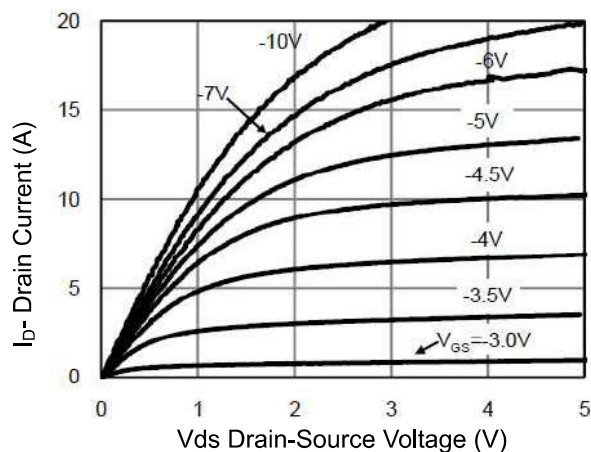


Figure 3 Output Characteristics

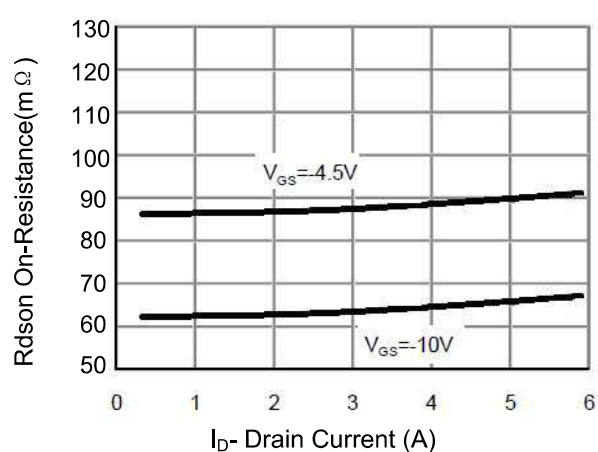


Figure 4 Drain-Source On-Resistance

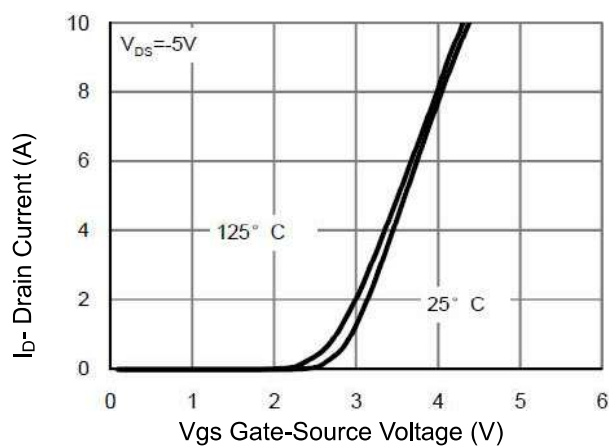


Figure 5 Transfer Characteristics

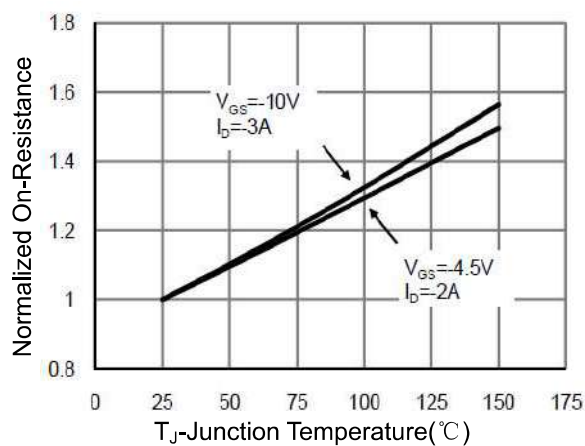
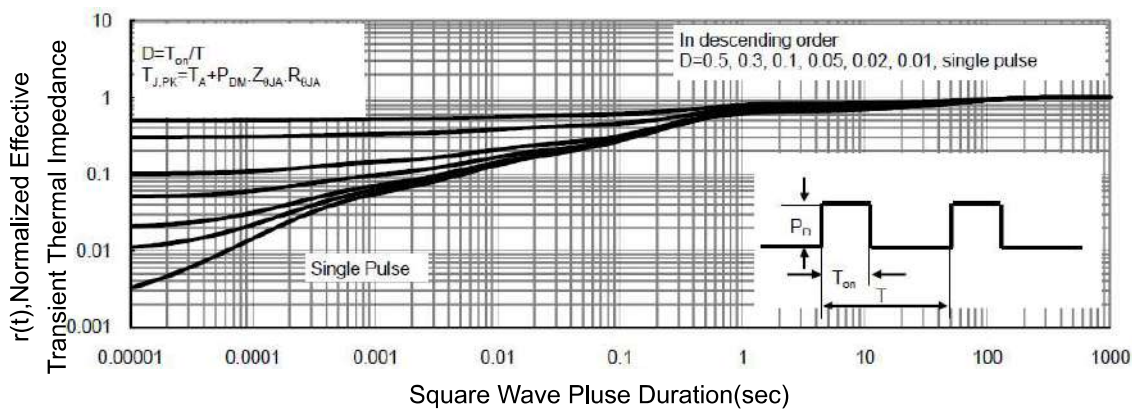
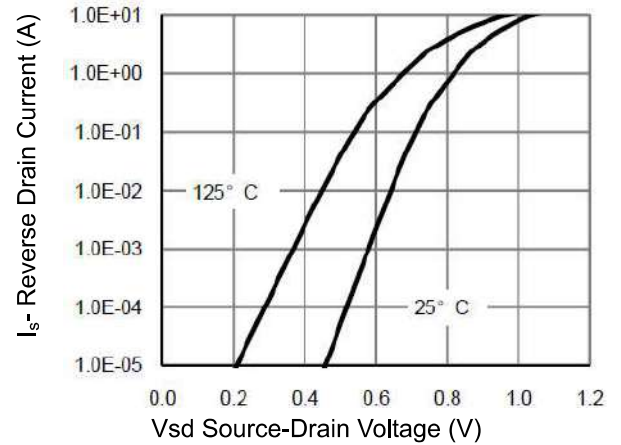
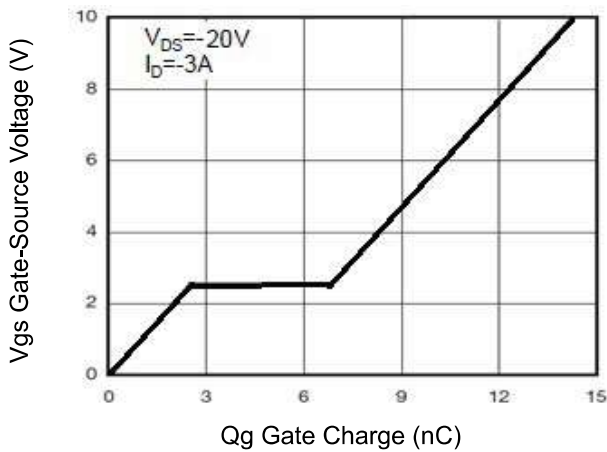
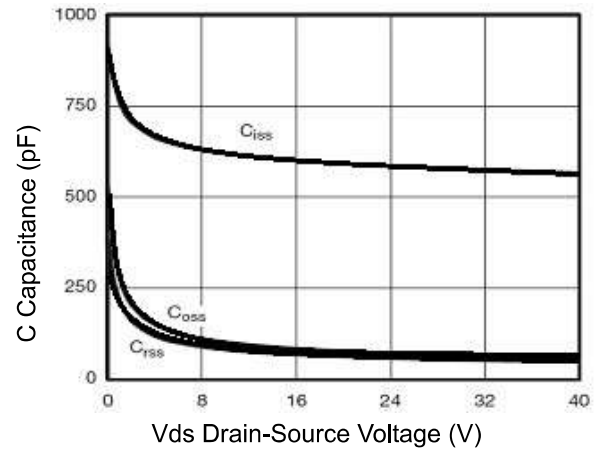
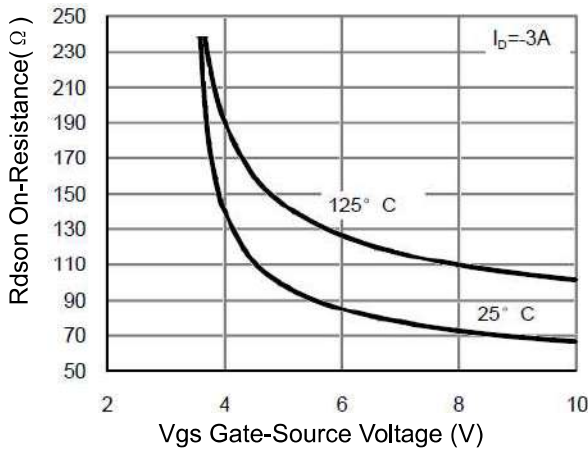
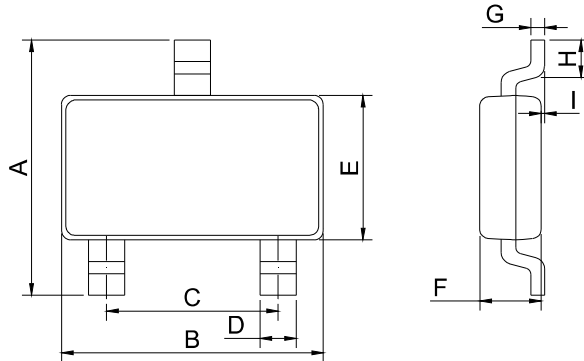


Figure 6 Drain-Source On-Resistance

Typical Electrical and Thermal Characteristics



SOT-23 Package Information



SOT-23

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.30	2.40	2.50	0.091	0.095	0.098
B	2.80	2.90	3.00	0.110	0.114	0.118
C	1.90 REF			0.075 REF		
D	0.35	0.40	0.45	0.014	0.016	0.018
E	1.20	1.30	1.40	0.047	0.051	0.055
F	0.90	1.00	1.10	0.035	0.039	0.043
G		0.10	0.15		0.004	0.006
H	0.20			0.008		
I	0		0.10	0		0.004